INMP Review Meeting

Date: November 17, Thursday, 2016 Time: 8:30am – 4:00 pm

Location: Cypress Semiconductor Auditorium, Paul Allen Building, Stanford University

Agenda

	Agenda	
8:00am	Continental Breakfast	
8:30	2D Materials, Contacts and Interconnects I	Chair: Yoshio Nishi
8:35	Unipolar n-Type Black Phosphorus Transistors with Scandium Contacts	Fiona Wang
8:55	Electronic Properties and Contact Engineering of Black Phosphorus: Insight from Ab-Initio Simulations	Yi-Chia Tsai and Blanka Magyari Kope
9:15	2D Materials, Contacts and Interconnects II	Chair: Philip Wong
9:20	BEOL Compatible Graphene/Cu Composites for Better Interconnect	Ling Li
9:40	Contact Engineering in n-Type MoTe ₂ Transistors	Michal Mleczko
10:00	Comparing Surface and Edge Contacts on Large Area MoS ₂	Alvin Tang
10:20	Break	
10:40	High Performance CMOS	Chair: Krishna Saraswat
11:00	Low Resistance Contacts to Nanoscale MOSFETs	Pranav Ramesh,
11:05	Nanoscale Ge NMOSFET	Junkyo Suh
11:25	System Level Performance Analysis of Transistor and Interconnect at 5nm Node	Vince Lee
11:45	Antimonide Based III-V MOSFET Integration on Si	Archana Kumar
12:05pm	Lunch	
1:00	Interface Defect Passivation and Dielectric Design	Chair: Paul McIntyre
1:05	Hydrogen Depassivation of Defects and Reliability of High-k/InGaAs MOS	Kechao Tang
1:25	Ge-Sn Nanowires and Electrochemical Characterization of Nanowire Interface States	Andrew Meng
1:45	Break for Poster Preparation	
2:00	Student Posters	
	All students under INMP funding will have posters.	All Students
3:00	AdCom and Faculty Meeting (Closed Session) in Allen 101, Linville conference room	AdCom members and Faculty only
4:00	Adjourn	
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Poster presentations

All oral presentation speakers will have posters.